

**INFORMATION DISCLOSURE STATEMENT**  
 PTO Form 1449

 Docket Number  
 01770.0002-US-01

 Serial Number  
 To Be Assigned

 Applicant(s)  
 Park et al.

 Filing Date  
 August 26, 2003

 Group Art Unit  
 To Be Assigned

**U.S. PATENT DOCUMENTS**

EXAMINER INITIALS	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE (IF APPROPRIATE)
TT	A	5,274,588	12/28/93	Manzur, et al.			
TT	B	5,494,838	02/27/96	Chang, et al.			
TT	C	5,508,955	04/16/96	Zimmer, et al.			
TT	D	6,013,552	01/11/00	Oyama			
TT	E	5,856,223	01/05/99	Wang			
TT	F	6,281,545	08/28/01	Liang, et al.			
TT	G	6,329,248	12/11/01	Yang			
TT	H	6,365,449	04/02/02	Kuo, et al.			
TT	I	6,538,276	03/25/03	Hsieh, et al.			

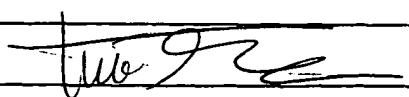
**FOREIGN PATENT DOCUMENTS**

EXAMINER INITIALS	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
							YES	NO

**OTHER DOCUMENTS**

TT	J	U.S. Patent Application Serial Number 10/358,645 entitled "VIRTUAL GROUND SINGLE TRANSISTOR MEMORY CELL, MEMORY ARRAY INCORPORATING SAME AND METHOD OF OPERATION THEREOF", filed February 4, 2003.						
TT	K	Yamauchi, Yoshimitsu, et al., "A New Cell Structure for Sub-quarter Micron High Density Flash Memory", 1995 International Electron Devices Meeting TECHNICAL DIGEST, IEEE, pp. 267-270, December 10-13, 1995.						

Examiner:



Date Considered:

01/05